

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

The **ASI UFT30-28S** is Designed for

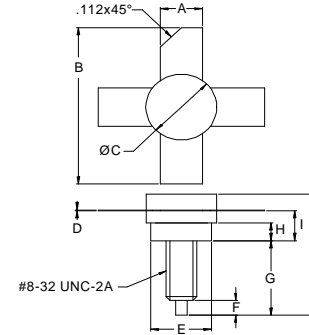
## FEATURES:

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- **Omnigold™** Metalization System

## MAXIMUM RATINGS

<b>I<sub>C</sub></b>	10 A
<b>V<sub>CB</sub></b>	60 V
<b>V<sub>CE</sub></b>	35 V
<b>P<sub>DISS</sub></b>	140 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	1.5 °C/W

## PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

**ORDER CODE: ASI10666**

## CHARACTERISTICS T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV <sub>CEO</sub>	I <sub>C</sub> = 50 mA			35			V
BV <sub>CER</sub>	I <sub>C</sub> = 50 mA	R <sub>BE</sub> = 10 Ω		60			V
BV <sub>EBO</sub>	I <sub>E</sub> = 10 mA			4.0			V
I <sub>CES</sub>	V <sub>E</sub> = 28 V					5	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5.0 V	I <sub>C</sub> = 1.0 A		10		100	---
C <sub>ob</sub>	V <sub>CB</sub> = 28 V f = 1.0 MHz					80	pF
P <sub>GE</sub>	V <sub>CE</sub> = 25 V	I <sub>CQ</sub> = 3.2 A	f = 225 MHz	13.5	14.5	-55	dB
IMD <sub>3</sub>	P <sub>REF</sub> = 16 W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB				dBc